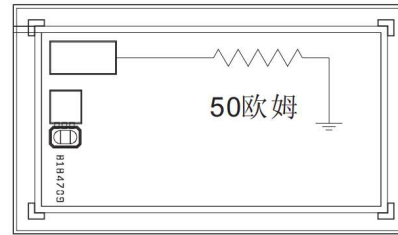


Performance

- Frequency: 8~12GHz
- Input Return Loss: -20dB
- Power Handling: 20W (8ms, 40% D.C)
- Chip size: 1.2*0.7*0.08mm

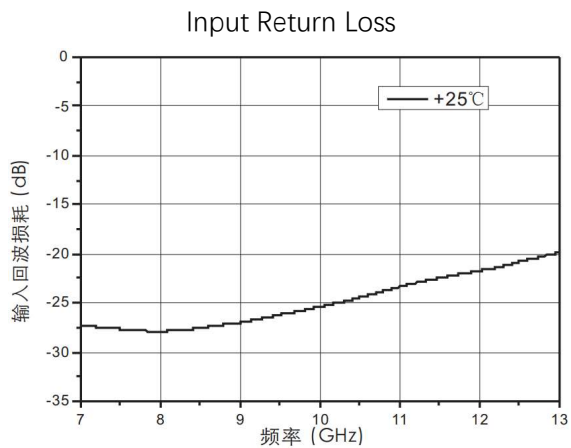
Function Diagram



Electrical Specifications (TA=+25°C, 50Ω system)

Parameter	Min	Typical	Max	Unit
Frequency Range	8~12			GHz
Input Return Loss	-	20	-	dB
Power Handling	-	-	20 (8ms, 40% D.C)	W

Test Curves (Die chip testing)



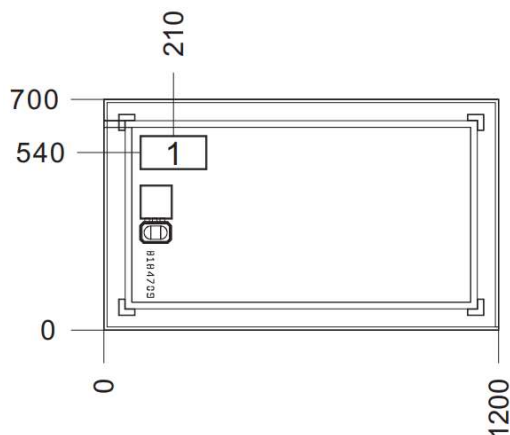
Absolute Max Ratings

Max Handling Power	20W (8ms, 40%)
Junction Temperature	200°C
Sintering Temperature (20 sec, N ₂ protection)	320°C
Storage Temperature	-55~+150°C
Operating Temperature	-55~+125°C
Static Protection Grade	Class 1A



ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS

Outline Size

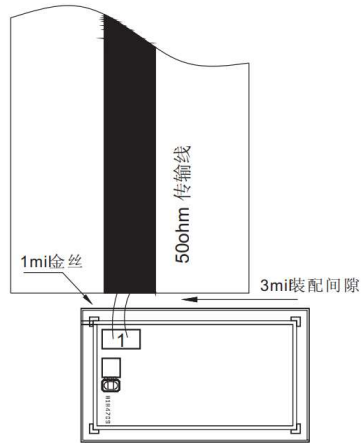


Note:

Unit: μm

1. Bottom side is gold plated
2. Bottom side is GND
3. Bonding pads is gold plated: 200*100μm
4. Don't bonding on thru holes
5. Tolerance: ±50μm

Assembly Drawing



Typical assemble gap: 0.076~0.152mm (3~6mils)

Bonding Pads Definition

Number	Symbol	Description
1	RFin	RF input port 50 ohm impedance
Bottom	GND	Bottom side of chip must be grounded